**Amendments to the Specification:**

Please replace the paragraph beginning at page 6, line 16, with the following amended paragraph:

A layer of acrylic resin 102 is formed on this PET film 101. As an example, a methyl ester of acrylic acid can be used as the acrylic resin. This acrylic resin layer 102 acts to prevent precipitation of oligomers on the surface of the PET film 101 in processes conducted later. The acrylic resin layer 102 also serves to planarize the uneven surface of the PET film [[102]] 101. Generally, PET film surface has unevenness of the order of several hundreds of angstroms to 1 μm. Such unevenness greatly affects the electrical properties of the semiconductor layer having a thickness of several hundreds of angstroms. Therefore, it is quite important to planarize the base on which the semiconductor layer is formed.

Please replace the paragraph beginning at page 7, line 30, with the following amended paragraph:

Thereafter, an n-type amorphous silicon film 107 is formed to a thickness of 300 Å by parallel-plate plasma-assisted CVD under the following conditions:

| | |
|---|---|
| film formation temperature (at which the substrate is heated): | 160°C |
| reaction pressure: | 0.5 torr |
| RF power (13.56 MHz): | 20 $mW/cm^2$ |
| reactant gases: | [[$B_2H_6$]] $PH_3/SiH_4$ = 1/100 |

Please replace the paragraph beginning at page 10, line 6, with the following amended paragraph:

Then, an n-type amorphous silicon film is grown to a thickness of 300 Å by the parallel-plate plasma-CVD machine under the following conditions:

| | |
|---|---|
| film formation temperature (at which the substrate is heated): | 160°C |
| reaction pressure: | 0.5 torr |
| RF power (13.56 MHz): | 20 mW/cm$^2$ |
| reactant gases: | [[$B_2H_6$]] $\underline{PH_3}$/$SiH_4$ = 1/100 |

Please replace the paragraph beginning at page 11, line 8, with the following amended paragraph:

The conditions under which an n-type microcrystalline silicon film is grown are described below. Also in this case, a parallel-plate plasma-CVD machine is used.

| | |
|---|---|
| film formation temperature (at which the substrate is heated): | 160°C |
| reaction pressure: | 0.5 torr |
| RF power (13.56 MHz): | 150 mW/cm$^2$ |
| reactant gases: | [[$B_2H_6$]] $\underline{PH_3}$/$SiH_4$ = 1/100 |